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#### **Features**

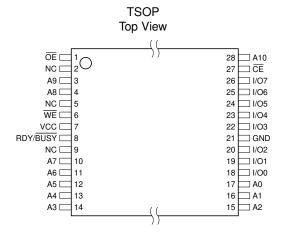
- · 2.7 to 3.6V Supply
  - Full Read and Write Operation
- · Low Power Dissipation
  - 8 mA Active Current
  - 50 μA CMOS Standby Current
- · Read Access Time 250 ns
- · Byte Write 3 ms
- Direct Microprocessor Control
  - DATA Polling
  - READ/BUSY Open Drain Output on TSOP
- High Reliability CMOS Technology
  - Endurance: 100,000 Cycles
  - Data Retention: 10 Years
- Low Voltage CMOS Compatible Inputs and Outputs
- · JEDEC Approved Byte Wide Pinout
- · Commercial and Industrial Temperature Ranges

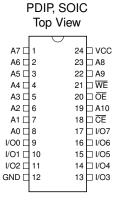
## **Description**

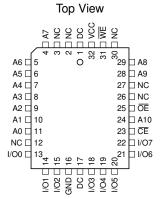
The AT28BV16 is a low-power, high-performance Electrically Erasable and Programmable Read Only Memory with easy to use features. The AT28BV16 is a 16K memory organized as 2,048 words by 8 bits. The device is manufactured with Atmel's reliable nonvolatile CMOS technology. *(continued)* 

## **Pin Configurations**

Pin Name	Function
A0 - A10	Addresses
CE	Chip Enable
ŌE	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
RDY/BUSY	Ready/Busy Output
NC	No Connect
DC	Don't Connect







**PLCC** 



16K (2K x 8)

Battery-Voltage<sup>™</sup>

Parallel

EEPROMs

**AT28BV16** 

Rev. 0380B-10/98



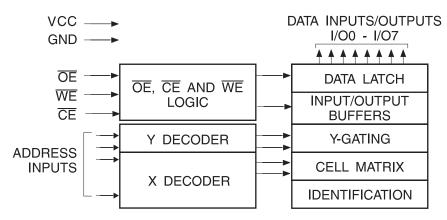


The AT28BV16 is accessed like a static RAM for the read or write cycles without the need of external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The end of a write cycle can be determined by DATA polling of I/O<sub>7</sub>. Once the end of a write cycle has been detected, a new access for a read or a write can begin.

The CMOS technology offers fast access times of 250 ns at low power dissipation. When the chip is deselected the standby current is less than 50  $\mu$ A.

Atmel's 28BV16 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32-bytes of EEPROM are available for device identification or tracking.

#### **Block Diagram**



## **Absolute Maximum Ratings\***

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including NC Pins) with Respect to Ground0.6V to +6.25V
All Output Voltages with Respect to Ground0.6V to $V_{\text{CC}}$ + 0.6V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground0.6V to +13.5V

\*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

### **Device Operation**

**READ:** The AT28BV16 is accessed like a Static RAM. When  $\overline{CE}$  and  $\overline{OE}$  are low and  $\overline{WE}$  is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever  $\overline{CE}$  or  $\overline{OE}$  is high. This dual line control gives designers increased flexibility in preventing bus contention.

**BYTE WRITE:** Writing data into the AT28BV16 is similar to writing into a Static RAM. A low pulse on the  $\overline{\text{WE}}$  or  $\overline{\text{CE}}$  input with  $\overline{\text{OE}}$  high and  $\overline{\text{CE}}$  or  $\overline{\text{WE}}$  low (respectively) initiates a byte write. The address location is latched on the last falling edge of  $\overline{\text{WE}}$  (or  $\overline{\text{CE}}$ ); the new data is latched on the first rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of  $t_{\text{WC}}$ , a read operation will effectively be a polling operation.

**DATA POLLING:** The AT28BV16 provides DATA POLL-ING to signal the completion of a write cycle. During a write cycle, an attempted read of the data being written results in

the complement of that data for  $I/O_7$  (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

**READY/BUSY** (TSOP only): READY/BUSY is an open drain output; it is pulled low during the internal write cycle and released at the completion of the write cycle.

**WRITE PROTECTION:** Inadvertent writes to the device are protected against in the following ways: (a)  $V_{CC}$  sense—if  $V_{CC}$  is below 2.0V (typical) the write function is inhibited; (b)  $V_{CC}$  power on delay—once  $V_{CC}$  has reached 2.0V the device will automatically time out 5 ms (typical) before allowing a byte write; and (c) Write Inhibit—holding any one of  $\overline{OE}$  low,  $\overline{CE}$  high or  $\overline{WE}$  high inhibits byte write cycles.

**DEVICE IDENTIFICATION:** An extra 32-bytes of EEPROM memory are available to the user for device identification. By raising A9 to  $12\pm0.5V$  and using address locations 7E0H to 7FFH the additional bytes may be written to or read from in the same manner as the regular memory array.





# **DC and AC Operating Range**

		AT28BV16-25	AT28BV16-30
Operating	Com.	0°C - 70°C	0°C - 70°C
Operating Temperature (Case)	Ind.	-40°C - 85°C	-40°C - 85°C
V <sub>CC</sub> Power Supply	·	2.7V to 3.6V	2.7V to 3.6V

# **Operating Modes**

Mode	CE	ŌĒ	WE	I/O
Read	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>
Write <sup>(2)</sup>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	D <sub>IN</sub>
Standby/Write Inhibit	V <sub>IH</sub>	X <sup>(1)</sup>	Х	High Z
Write Inhibit	Х	Х	V <sub>IH</sub>	
Write Inhibit	Х	V <sub>IL</sub>	Х	
Output Disable	Х	V <sub>IH</sub>	Х	High Z

Notes: 1. X can be V<sub>IL</sub> or V<sub>IH</sub>.

2. Refer to AC Programming Waveforms.

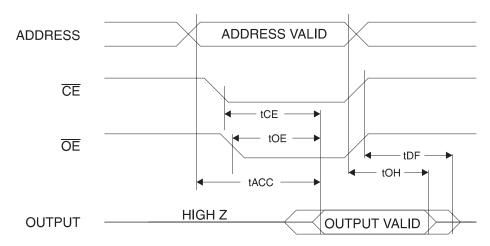
## **DC Characteristics**

Symbol	Parameter	Condition	Min	Max	Units
I <sub>LI</sub>	Input Load Current	$V_{IN} = 0V$ to $V_{CC} + 1.0V$		5	μΑ
I <sub>LO</sub>	Output Leakage Current	$V_{I/O} = 0V \text{ to } V_{CC}$		5	μΑ
I <sub>SB</sub>	V <sub>CC</sub> Standby Current CMOS	$\overline{\text{CE}}$ = V <sub>CC</sub> - 0.3V to V <sub>CC</sub> + 1.0V		50	μΑ
I <sub>cc</sub>	V <sub>CC</sub> Active Current AC	f = 5 MHz; I <sub>OUT</sub> = 0 mA; CE = V <sub>IL</sub>		8	mA
V <sub>IL</sub>	Input Low Voltage			0.6	V
$V_{IH}$	Input High Voltage		2.0		V
V	Outrout Law Valtage	I <sub>OL</sub> = 1 mA		0.3	V
V <sub>OL</sub>	Output Low Voltage	$I_{OL} = 2 \text{ mA for RDY/}\overline{BUSY}$		0.3	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -100 μA	2.0		V

#### **AC Read Characteristics**

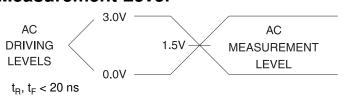
			AT28BV16-25		AT28BV16-30	
Symbol	Parameter	Min	Max	Min	Max	Units
t <sub>ACC</sub>	Address to Output Delay		250		300	ns
t <sub>CE</sub> <sup>(1)</sup>	CE to Output Delay		250		300	ns
t <sub>OE</sub> <sup>(2)</sup>	OE to Output Delay		100		100	ns
t <sub>DF</sub> <sup>(3)(4)</sup>	CE or OE High to Output Float	0	55	0	55	ns
t <sub>OH</sub>	Output Hold from $\overline{OE}$ , $\overline{CE}$ or Address, whichever occurred first	0		0		ns

# AC Read Waveforms<sup>(1)(2)(3)(4)</sup>

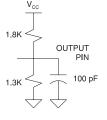


- Notes: 1.  $\overline{CE}$  may be delayed up to  $t_{ACC}$   $t_{CE}$  after the address transition without impact on  $t_{ACC}$ .
  - 2.  $\overline{\text{OE}}$  may be delayed up to  $t_{\text{CE}}$   $t_{\text{OE}}$  after the falling edge of  $\overline{\text{CE}}$  without impact on  $t_{\text{CE}}$  or by  $t_{\text{ACC}}$   $t_{\text{OE}}$  after an address change without impact on  $t_{ACC}$ .
  - 3.  $t_{DF}$  is specified from  $\overline{OE}$  or  $\overline{CE}$  whichever occurs first ( $C_L = 5 \text{ pF}$ ).
  - 4. This parameter is characterized and is not 100% tested.

### **Input Test Waveforms and Measurement Level**



## **Output Test Load**



## Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$ 

Symbol	Тур	Max	Units	Conditions
C <sub>IN</sub>	4	6	pF	$V_{IN} = 0V$
C <sub>OUT</sub>	8	12	pF	$V_{OUT} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.



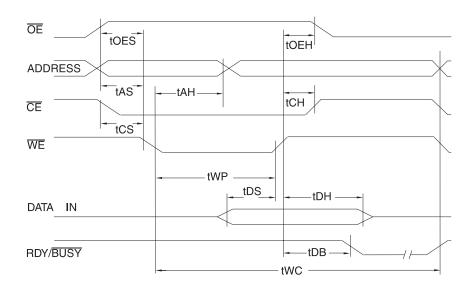


## **AC Write Characteristics**

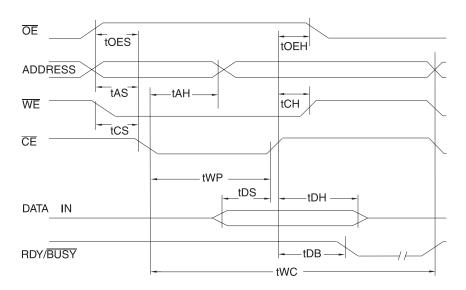
Symbol	Parameter	Min	Max	Units
t <sub>AS</sub> , t <sub>OES</sub>	Address, OE Set-up Time	10		ns
t <sub>AH</sub>	Address Hold Time	100		ns
t <sub>WP</sub>	Write Pulse Width (WE or CE)	150	1000	ns
t <sub>DS</sub>	Data Set-up Time	100		ns
t <sub>DH</sub> , t <sub>OEH</sub>	Data, OE Hold Time	10		ns
t <sub>CS</sub> , t <sub>CH</sub>	CE to WE and WE to CE Set-up and Hold Time	0		ns
t <sub>WC</sub>	Write Cycle Time		3.0	ms
t <sub>DB</sub>	Time to Device Busy		50	ns

## **AC Write Waveforms**

## **WE** Controlled



### **CE** Controlled



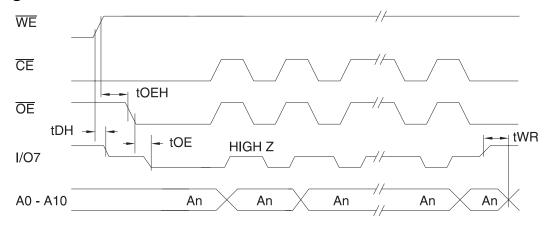
# **Data** Polling Characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Тур	Max	Units
t <sub>DH</sub>	Data Hold Time	10			ns
t <sub>OEH</sub>	OE Hold Time	10			ns
t <sub>OE</sub>	ŌĒ to Output Delay <sup>(2)</sup>				ns
t <sub>WR</sub>	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See AC Characteristics.

## **Data** Polling Waveforms







# **Ordering Information**<sup>(1)</sup>

	I <sub>cc</sub>	(mA)			
t <sub>ACC</sub> (ns)	Active	Standby	Ordering Code	Package	Operation Range
250	8	0.05	AT28BV16-25TC	28T	Commercial
			AT28BV16-25JC	32J	(0°C to 70°C)
			AT28BV16-25PC	24P6	
			AT28BV16-25SC	24S	
	8	0.05	AT28BV16-25TI	28T	Industrial
			AT28BV16-25JI	32J	(-40°C to 85°C)
			AT28BV16-25PI	24P6	
			AT28BV16-25SI	24S	
300	8	0.05	AT28BV16-30TC	28T	Commercial
			AT28BV16-30JC	32J	(0°C to 70°C)
			AT28BV16-30PC	24P6	
			AT28BV16-30SC	24S	
	8	0.05	AT28BV16-30TI	28T	Industrial
			AT28BV16-30JI	32J	(-40°C to 85°C)
			AT28BV16-30PI	24P6	
			AT28BV16-30SI	24S	

Note: 1. See Valid Part Number table below.

## **Valid Part Numbers**

The following table lists standard Atmel products that can be ordered.

Device Numbers Speed Package and Temperature Combinations		Package and Temperature Combinations
AT28BV16	25	JC, JI, PC, PI, SC, SI, TC, TI
AT28BV16	30	JC, JI, PC, PI, SC, SI, TC, TI

## **Die Products**

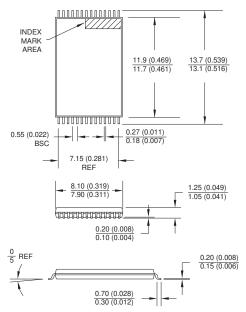
Reference Section: Parallel EEPROM Die Products

	Package Type				
28T	28-Lead, Plastic Thin Small Outline Package (TSOP)				
32J	32-Lead, Plastic J-Leaded Chip Carrier (PLCC)				
24P6	24-Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)				
24S	24-Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)				

## **Packaging Information**

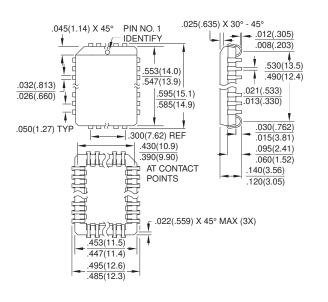
**28T**, 28-Lead, Plastic Thin Small Outline Package (TSOP)

Dimensions in Millimeters and (Inches)\*



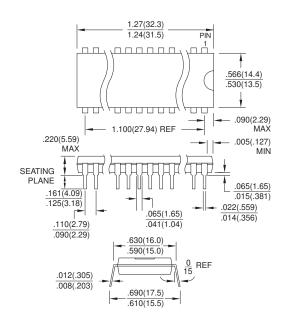
\*Controlling dimension: millimeters

**32J**, 32-Lead, Plastic J-Leaded Chip Carier (PLCC) Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-016 AE



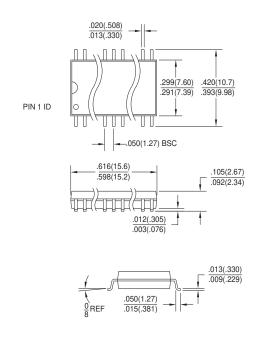
**24P6**, 24-Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)

Dimensions in Inches and (Millimeters)
JEDEC STANDARD MS-011 AA



**24S**, 24-Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)

Dimensions in Inches and (Millimeters)











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